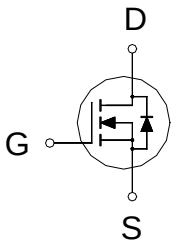
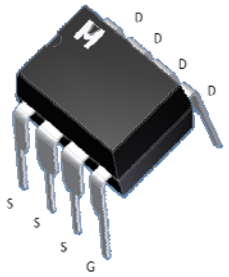
N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	100V
$R_{DSON\ (MAX.)}$	100mΩ
I_D	6A





UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A = 25 °C	I_D	6	A
	T_A = 100 °C		4.5	
Pulsed Drain Current[1]		I_{DM}	24	
Avalanche Current		I_{AS}	5	
Avalanche Energy	L = 0.1mH, ID=5A, RG=25Ω	E_{AS}	1.25	mJ
Repetitive Avalanche Energy[2]	L = 0.05mH	E_{AR}	0.625	
Power Dissipation	T_A = 25 °C	P_D	2.5	W
	T_A = 100 °C		1	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		25	°C / W
Junction-to-Ambient[3]	$R_{\theta JA}$		50	

[1]Pulse width limited by maximum junction temperature.

[2]Duty cycle ≤ 1%

[3]50°C / W when mounted on a 1 in^2 pad of 2 oz copper.

ELECTRICAL CHARACTERISTICS (T_C = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	1.8	3.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1	μA
		V_{DS} = 70V, V_{GS} = 0V, T_J = 125 °C			25	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 10V, V_{GS} = 10V	5			A
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 6A		90	100	mΩ
		V_{GS} = 5V, I_D = 3A		100	125	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 6A		9		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		1490		pF
Output Capacitance	C_{oss}			76		
Reverse Transfer Capacitance	C_{rss}			63		
Gate Resistance	R_g	V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz		1.7		Ω
Total Gate Charge[1,2]	Q_g	V_{DS} = 50V, V_{GS} = 10V, I_D = 6A		34		nC
Gate-Source Charge[1,2]	Q_{gs}			3.5		
Gate-Drain Charge[1,2]	Q_{gd}			9.2		
Turn-On Delay Time[1,2]	$t_{d(on)}$	V_{DS} = 50V, I_D = 1A, V_{GS} = 10V, R_{GS} = 6Ω		10		nS
Rise Time[1,2]	t_r			25		
Turn-Off Delay Time[1,2]	$t_{d(off)}$			20		
Fall Time[1,2]	t_f			20		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C = 25 °C)						
Continuous Current	I_S				2.5	A
Pulsed Current[3]	I_{SM}				10	
Forward Voltage[1]	V_{SD}	I_F = I_S, V_{GS} = 0V			1.3	V
Reverse Recovery Time	t_{rr}	I_F = 10A, dI_F/dt = 100A / μS		50		nS
Reverse Recovery Charge	Q_{rr}			85		nC

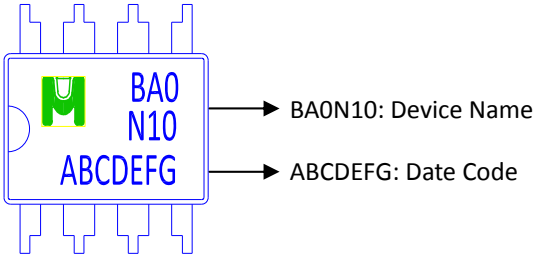
[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

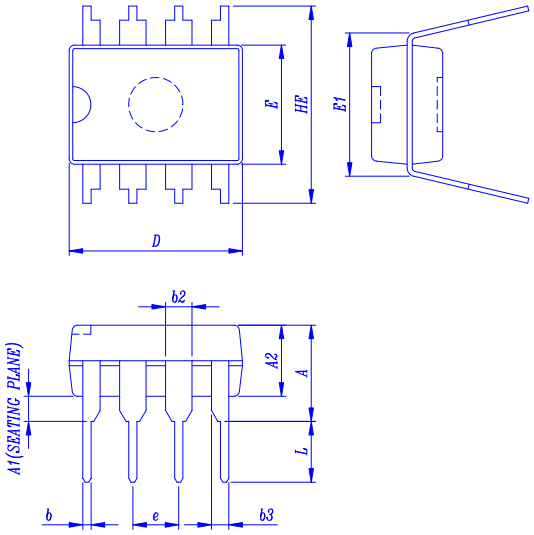
[3]Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: EMBA0N10S for DIP-8



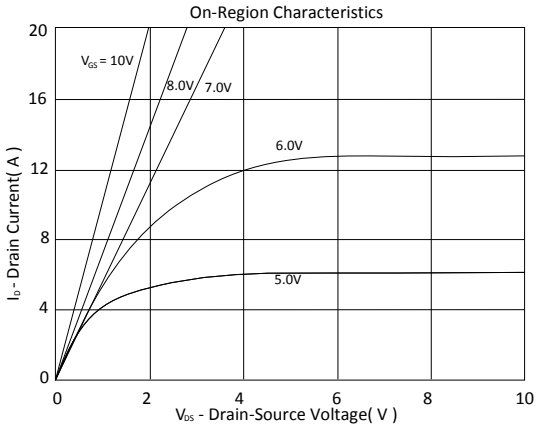
Outline Drawing

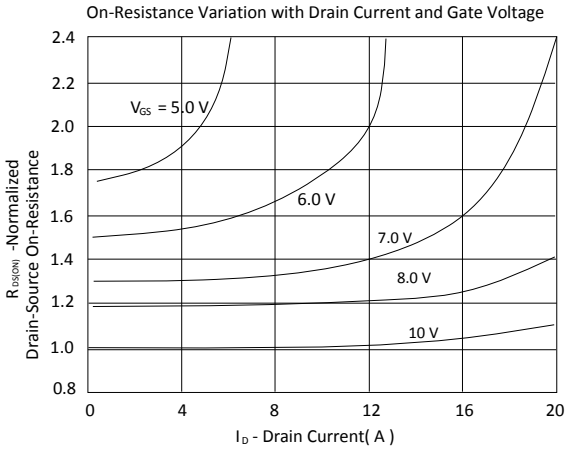


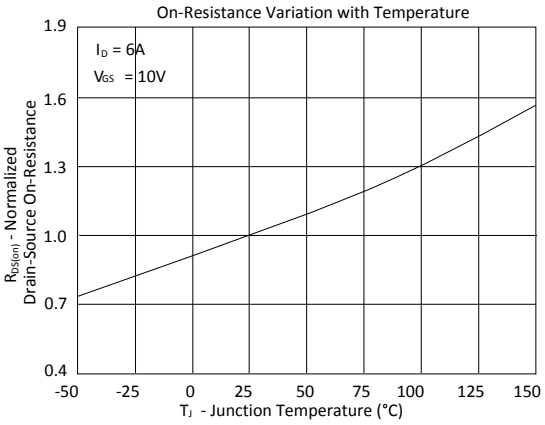
Dimension in mm

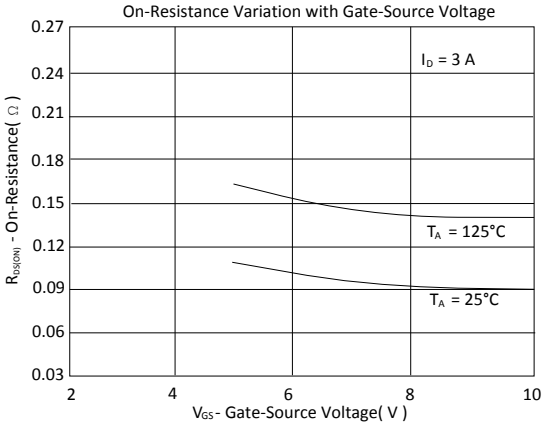
Dimension	A	A1	A2	b	b2	b3	c	D	E	E1	e	HE	L
in.		0.38	2.92	0.25	1.14	0.76	0.20	9.01	6.09	7.62			2.92
Typ.											2.54		
Max.	5.34		4.96	0.56	1.78	1.15	0.36	10.16	7.12	8.26		10.92	3.81

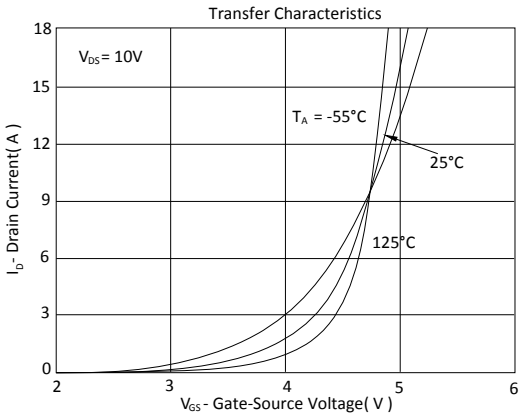
TYPICAL CHARACTERISTICS

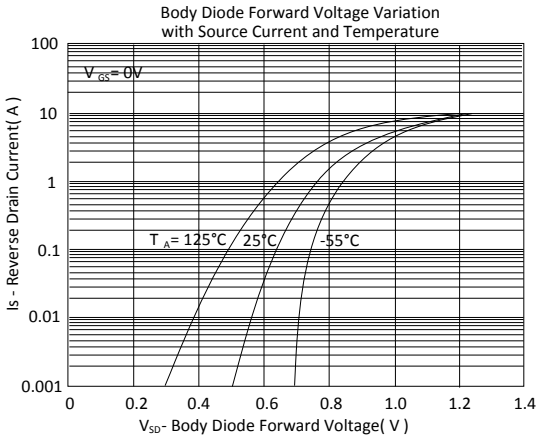




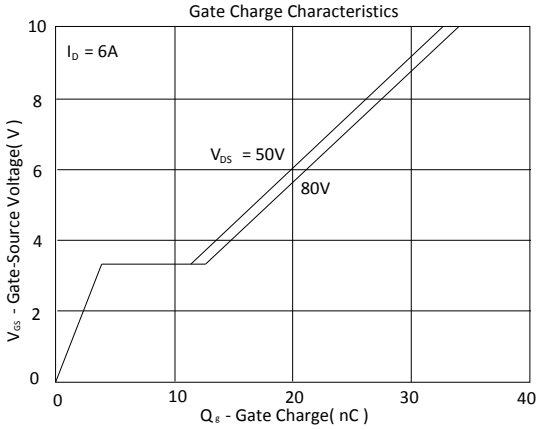




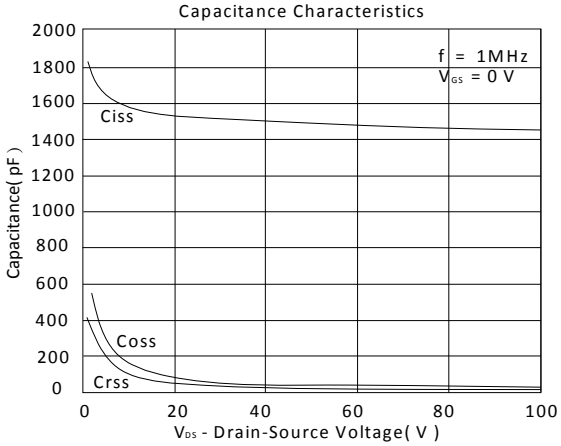




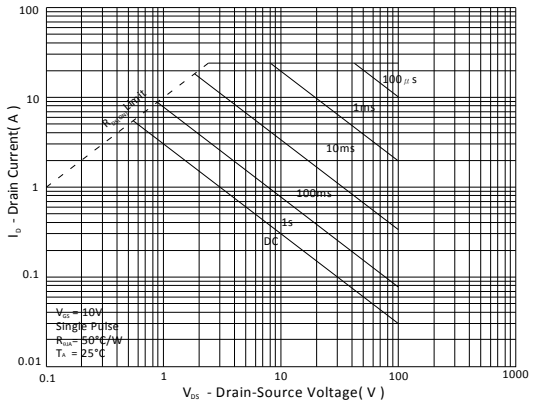
Gate Charge Characteristics



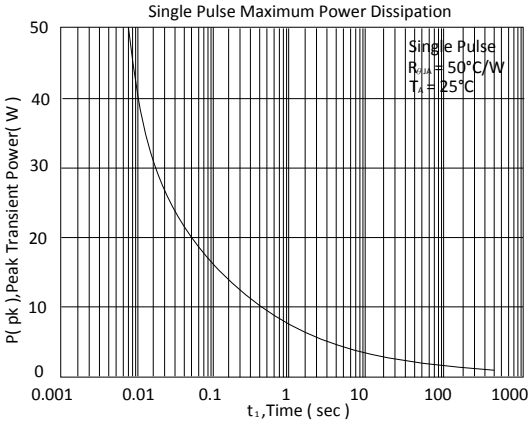
Capacitance Characteristics



Maximum Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve